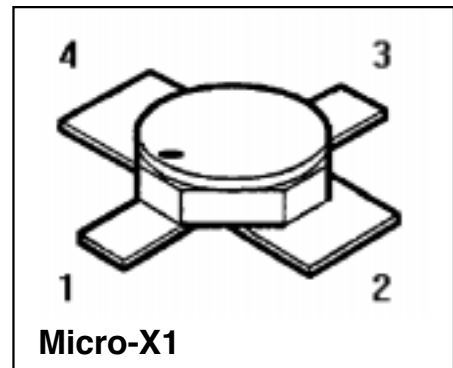


HiRel NPN Silicon RF Transistor

BFY 196

Features

- **HiRel Discrete and Microwave Semiconductor**
- For low noise, high gain amplifiers up to 2 GHz.
- For linear broadband amplifiers
- Hermetically sealed microwave package
- $f_T = 6.5$ GHz, $F = 3$ dB at 2 GHz
- ESA Qualification pending



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration				Package
BFY 196 (ql)	–	see below	C	E	B	E	Micro-X1

(ql) Quality Level: P: Professional Quality, Ordering Code: Q62702F1684

H: High Rel Quality, Ordering Code: on request

S: Space Quality, Ordering Code: on request

(see **Chapter Order Instructions** for ordering example)

Table 1 Maximum Ratings

Parameter	Symbol	Limit Values	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage, $V_{BE} = 0$	V_{CES}	20	V
Collector-base voltage	V_{CBO}	20	V
Emitter-base voltage	V_{EBO}	2	V
Collector current	I_C	100	mA
Base current	I_B	12 ¹⁾	mA
Total power dissipation, $T_S \leq 104$ °C ²⁾	P_{tot}	700	mW
Junction temperature	T_j	200	°C
Operating temperature range	T_{op}	– 65 ... + 200	°C
Storage temperature range	T_{stg}	– 65 ... + 200	°C

Thermal Resistance

Junction soldering point ²⁾	$R_{th JS}$	< 135	K/W
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¹⁾ The maximum permissible base current for V_{FBE} measurements is 50 mA (spot measurement duration < 1 s).

²⁾ T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics

Table 2 DC Characteristics at $T_A = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Collector-base cutoff current $V_{CB} = 20\text{ V}, I_E = 0$	I_{CBO}	–	–	100	μA
Collector-emitter cutoff current $V_{CE} = 12\text{ V}, I_B = 1\text{ }\mu\text{A}$ ³⁾	I_{CEX}	–	–	1000	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}, I_E = 0$	I_{CBO}	–	–	50	nA
Emitter-base cutoff current $V_{EB} = 2\text{ V}, I_C = 0$	I_{EBO}	–	–	25	μA
Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$	I_{EBO}	–	–	0.5	μA
Base-emitter forward voltage $I_E = 50\text{ mA}, I_C = 0$	V_{FBE}	–	–	1	V
DC current gain $I_C = 50\text{ mA}, V_{CE} = 8\text{ V}$	h_{FE}	50	100	175	–

³⁾ This test assures $V_{(BR)CE0} > 12\text{ V}$.

Table 3 AC Characteristics at $T_A = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Transition frequency $I_C = 70\text{ mA}, V_{CE} = 5\text{ V}, f = 500\text{ MHz}$	f_T	6	6.5	–	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}, V_{BE} = v_{be} = 0, f = 1\text{ MHz}$	C_{CB}	–	1	1.3	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}, V_{BE} = v_{be} = 0, f = 1\text{ MHz}$	C_{CE}	–	0.44	–	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, V_{CB} = v_{cb} = 0, f = 1\text{ MHz}$	C_{EB}	–	3.6	4.3	pF
Noise figure $I_C = 20\text{ mA}, V_{CE} = 5\text{ V}, f = 2\text{ GHz},$ $Z_S = Z_{Sopt}$	F	–	3	3.5	dB
Power gain $I_C = 70\text{ mA}, V_{CE} = 5\text{ V}, f = 2\text{ GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$	$G_{ma}^{4)}$	10	11	–	dB
Transducer gain $I_C = 70\text{ mA}, V_{CE} = 5\text{ V}, f = 2\text{ GHz},$ $Z_S = Z_L = 50\text{ }\Omega$	$ S_{21e} ^2$	4	5	–	dB
Output power $I_C = 80\text{ mA}, V_{CE} = 5\text{ V}, f = 2\text{ GHz},$ $P_{IN} = 15\text{ dBm}, Z_S = Z_L = 50\text{ }\Omega$	P_{out}	18.5	19.5	–	dBm

$$4) G_{ma} = \left| \frac{S_{21}}{S_{12}} \right| (k - \sqrt{k^2 - 1}), G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$$

Order Instructions

Full type variant including quality level must be specified by the orderer. For HiRel Discrete and Microwave Semiconductors the ordering code specifies device family and quality level.

Ordering Form:

Ordering Code: Q...
BFY196 (x) (ql)
(ql): Quality Level

Ordering Example:

Ordering Code: Q62702F1684
BFY196 P
For BFY196 in Professional Quality Level

Further Information

See our WWW-Pages:

- Discrete and RF-Semiconductors (Small Signal Semiconductors)
www.siemens.de/semiconductor/products/35/35.htm
- HiRel Discrete and Microwave Semiconductors
www.siemens.de/semiconductor/products/35/353.htm

Please contact also our marketing division:

Tel.: ++89 6362 4480

Fax.: ++89 6362 5568

e-mail: martin.wimmers@hl.siemens.de

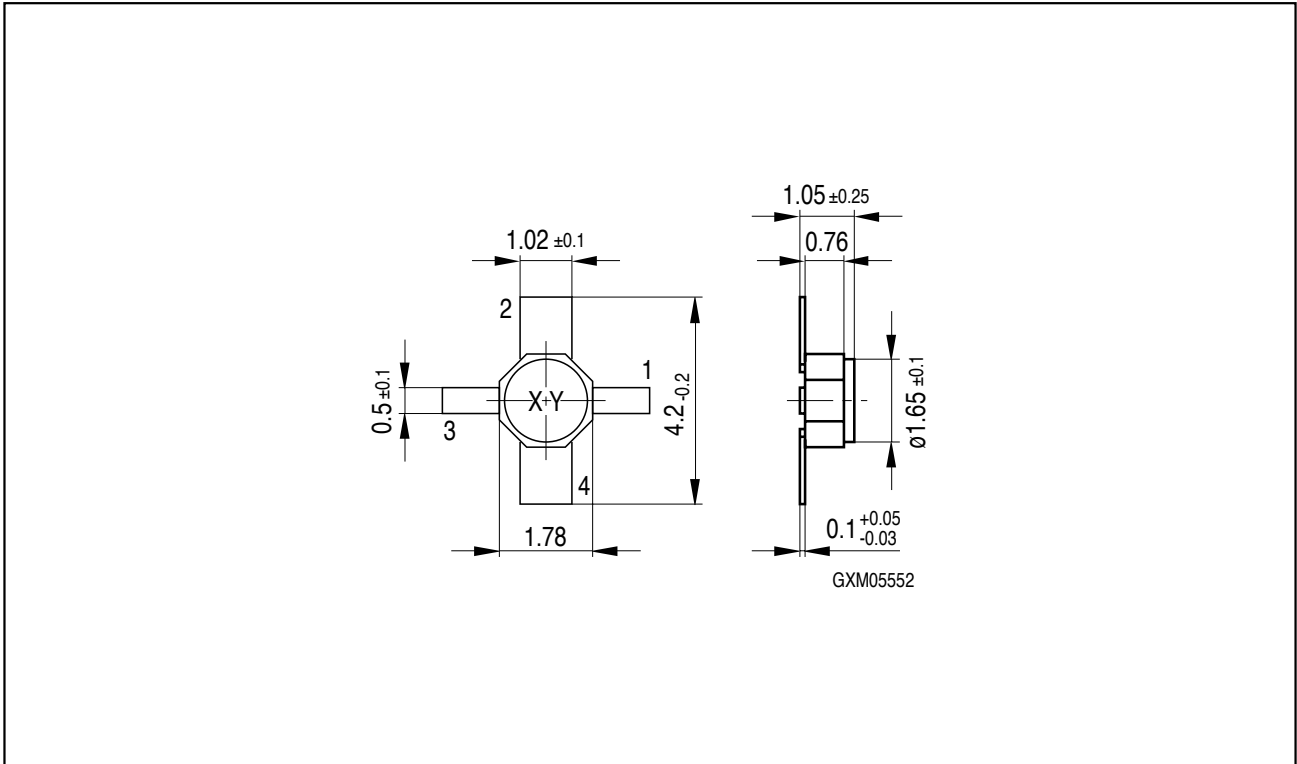


Figure 1 Micro-X1 Package